10Gb/s InGaAs PIN PD chip

WPP150CGP

Features

- 50µm active area for better optical alignment
- Date rate up to 10Gb/s
- High reliability

Absolute Maximum Ratings

Parameters	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Reverse current	I_R	3	mA
Operating case temperature range	T_{OP}	-40 to +85	°C
Storage temperature range	T_{STG}	-40 to +85	°C

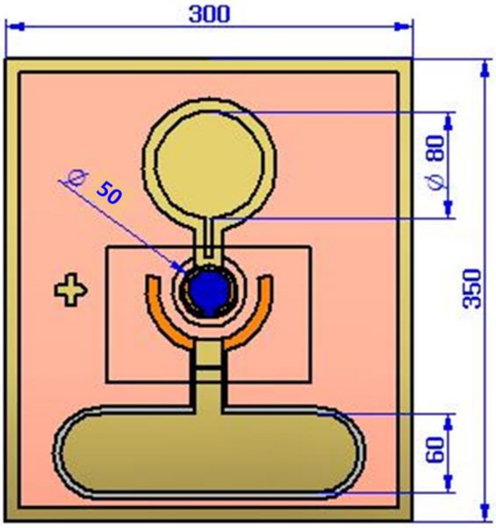
Electro-Optical Characteristics (Typical values are at 25 °C)

Parameters	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	I_D	V_R = 5V		3	10	nA
Capacitance	C_{PD}	V_R = 5V		0.25	0.3	pF
Wavelength	λ		1000		1650	nm
Responsivity	R	V_R = 5V, 1550nm	0.9	1.0		A/W
		V_R = 5V, 1310nm	0.8	0.9		
Sensitivity	Ps	11.125 Gb/s, ER 3.8dB, 10^{-12} BER, 1550nm 1)		-17		dBm
		2.488 Gb/s, ER 10dB 10^{-12} BER, 1550nm 2)		-30		dBm

1) Sensitivity depends on TIA
2) Coupled with super TIA for GPON application

Dimensions

Parameters	Symbol	Min.	Typ.	Max.	Unit
Light receiving area diameter	D		50		μm
Chip size	-		300x350		μm^2
Chip thickness	t	130	150	170	μm



TOP VIEW

(unit : μm)

SIDE VIEW

Ordering information

WPP150CGP

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Specifications described here are subject to change without notice